

Features

- Frequency: 20GHz~38GHz
- Gain: 8dB
- Output P_{1dB}: 18dBm
- Supply Voltage: +5~+6V
- Balanced Amplifier
- Die Size: 1.67mm×1.25mm×0.1mm

Typical Applications

- Point-to-Point Radios
- SATCOM
- Military and Space
- Test and Measurement
- LO Driver

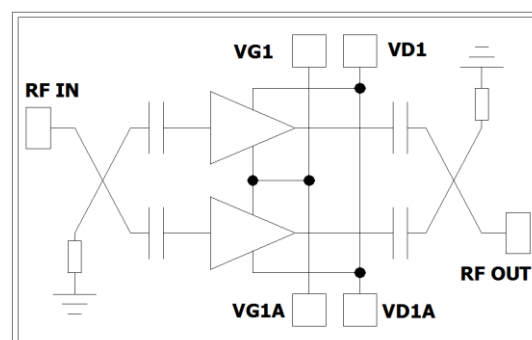
General Description

XT3912 is a wideband GaAs MMIC driver amplifier which operates between 20GHz~38GHz. The amplifier has moderate gain and output P_{1dB}, making it an ideally linear gain block or driver amplifier for microwave radios.

XT3912 is a balanced amplifier that has good input and output return loss when amplifier is turned off and on.

XT3912 offers full passivation for increased reliability and moisture protection.

Functional Diagram



Electrical Performance ($T_A=25^{\circ}\text{C}$, $V_D=+5\text{V}$, $I_D=100\text{mA}$, $Z_0=50\Omega$)

Parameter	Min.	Typ.	Max.	Units
Frequency Range	20~38			GHz
Gain	6	10	—	dB
Gain Flatness	—	1.5	—	dB
Reverse Isolation	—	-40	—	dB
Input/Output Return Loss	—	-17	—	dB
Noise Figure	—	5	—	dB
Output Power for 1 dB Compression (OP _{1dB})	—	18	—	dBm
Drain Voltage(V _D)	5	—	6	V
Supply Current(I _D)	—	100	150	mA

Absolute Maximum Ratings

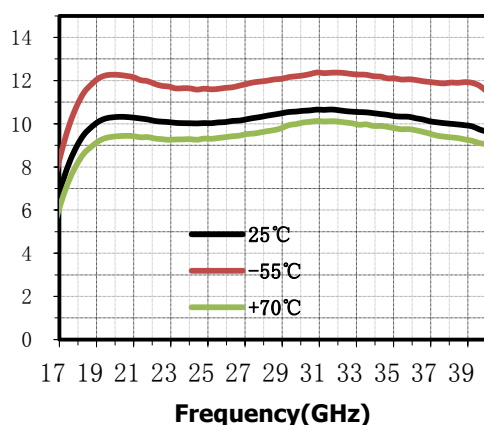
Maximum Input Power	+12dBm	Operating Temperature	-55℃~+85℃
Channel Temperature	+150℃	Storage Temperature	-65℃~+150℃
Maximum V _D	+6.5V	Maximum V _G	-1.2V

Typical Performance Curve

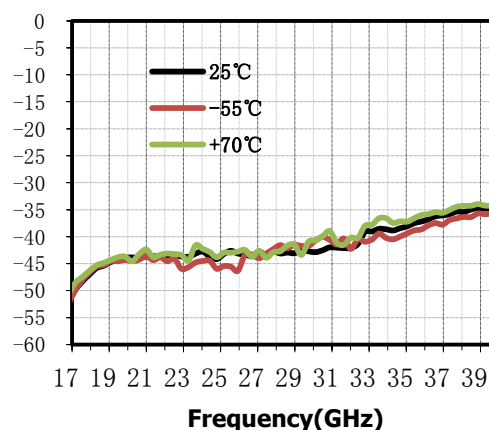
Data Based on the On-Wafer RF Probe Test Results

*Bias Conditions: $V_D = 5V$, $I_D = 100mA$

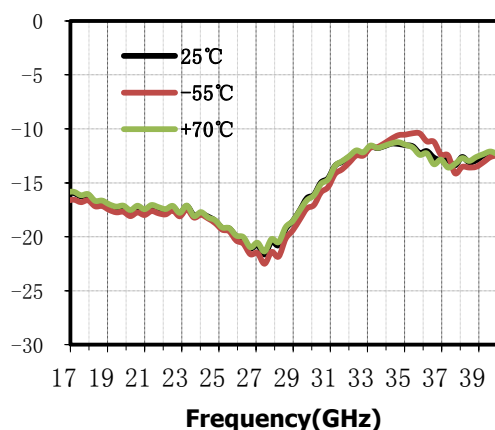
Small Signal Gain(dB) vs.Temperature



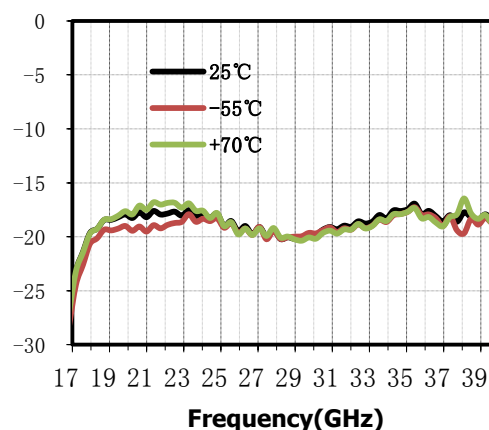
Reverse Isolation(dB) vs.Temperature



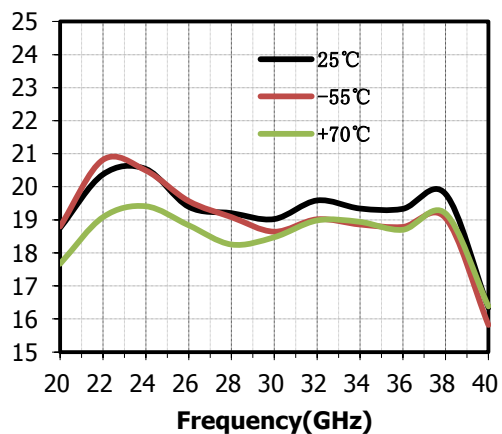
Input Return Loss(dB) vs.Temperature



Output Return Loss(dB) vs.Temperature

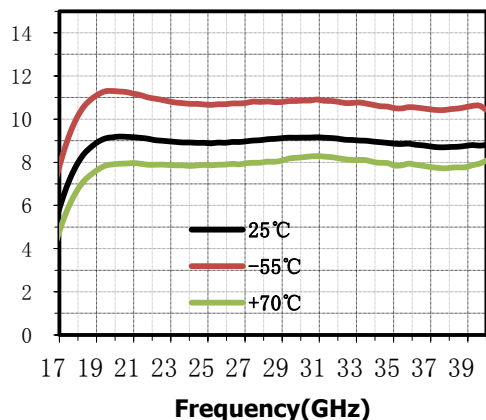


OP₁(dBm) vs.Temperature @ $V_D = 5V$

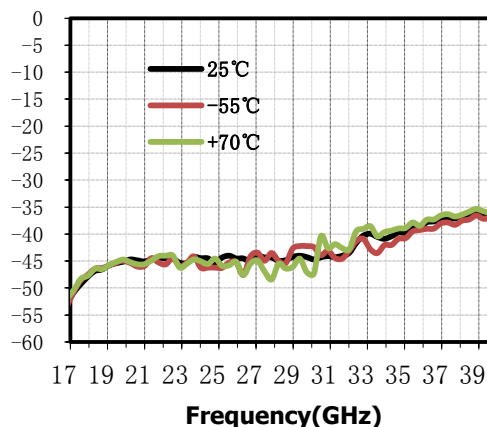


*Bias Conditions: $V_D = 6V$, $I_D = 100mA$

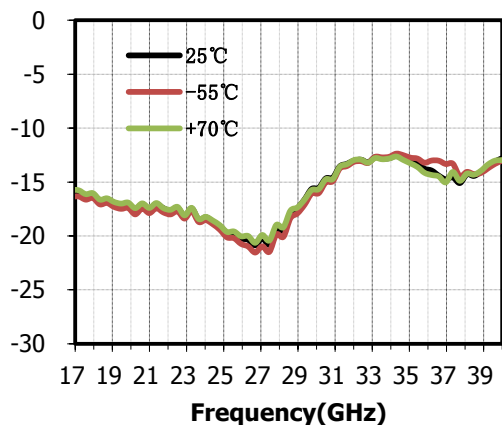
Small Signal Gain(dB) vs.Temperature



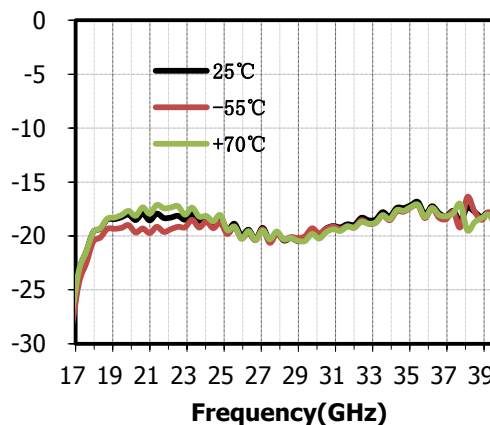
Reverse Isolation(dB) vs.Temperature



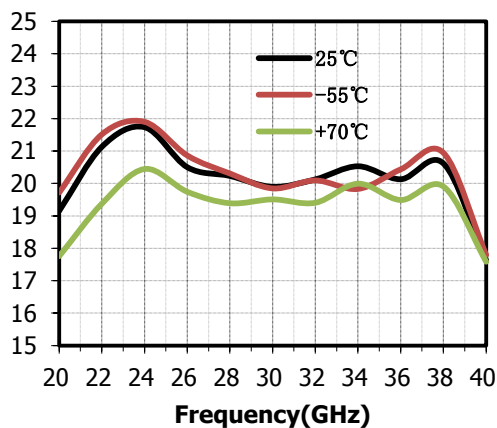
Input Return Loss(dB) vs.Temperature



Output Return Loss(dB) vs.Temperature



OP₁dB(dBm) vs.Temperature @ $V_D = 6V$



XT3912



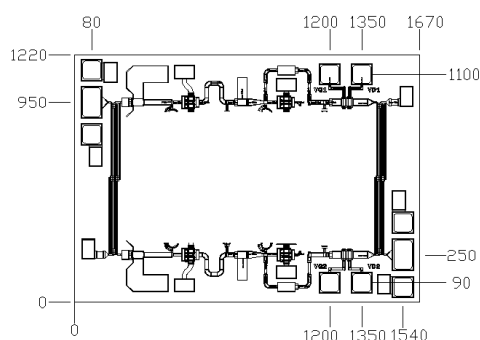
GaAs MMIC Driver Amplifier
20GHz~38GHz

Rev 2.0

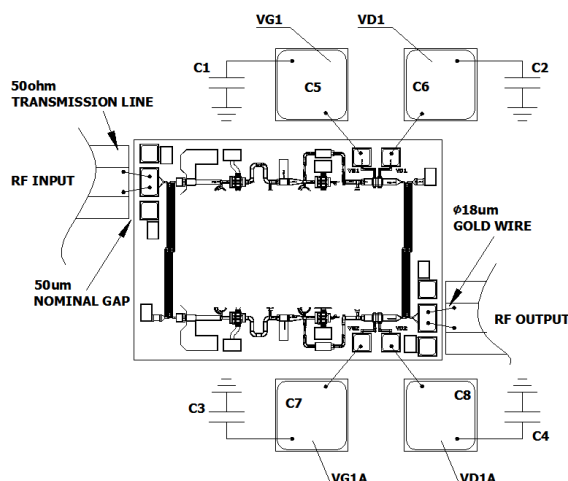
Die Outline (all dimensions in um)

RF Bonding pad size:100x150um

VG/VD bonding pas size :100x100um



Assembly Diagram



Components List

Reference Des.	Value	Part Number	Manuf.	Size
C1~C4	2.2uF	0603YD225KAT2A	AVX	0603
C5~C8	100pF	—	ANY	SLC

Notes

1. The XT3912 is biased with a positive drain voltage supply and negative gate voltage supply.
When the drain voltage is set to 5V, the recommended gate voltage is set to -0.5~-0.7 V.
2. RF connections should be made as short as possible to reduce the inductive effect of the bond wire.
3. The backside of the XT3912 is RF grounded. Die attach should be accomplished with electrically and thermally conductive epoxy only.
4. Bypass caps C1~C4 should be placed no more than 1.5mm from the amplifier.
5. Bond pads VG and VD exist on the upper and lower sides of the MMIC for assembly convenience.
For best performance the unused pad should be attached with a 100pF cap to ground.

Attention:

GaAs MMIC devices are susceptible to damage from electrostatic discharge. Proper precautions should be observed during handling, assembly and test.